

## Abstract of the Disclosure

The present invention is related to a method for fabricating a ferroelectric memory device effectively preventing a deformation and lift of a lower electrode caused by a different thermal expansion rate between the lower electrode and a inter layer dielectric film at a succeeding heat treatment process. The method for fabricating a ferroelectric memory device includes: forming a lower electrode on a predetermined surface of a semiconductor substrate; forming a metal oxide layer over a surface of the lower electrode and a surface of the semiconductor substrate; forming an inter layer dielectric film over the metal oxide layer; performing a blanket etching for the inter layer dielectric film and the metal oxide layer; and forming an opening having a predetermined depth.